

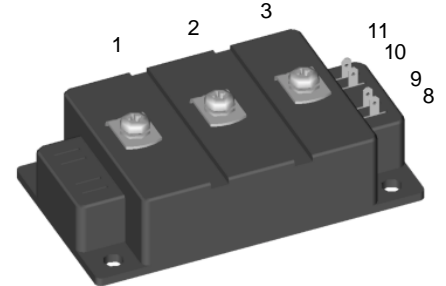
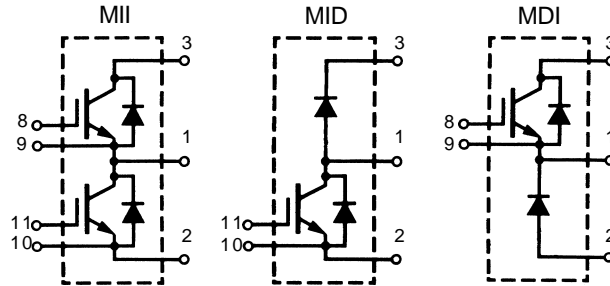
# IGBT Modules

Short Circuit SOA Capability  
Square RBSOA

$$I_{C25} = 270 \text{ A}$$

$$V_{CES} = 1200 \text{ V}$$

$$V_{CE(sat) \text{ typ.}} = 2.2 \text{ V}$$



Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 20 \text{ k}\Omega$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	270	A
$I_{C80}$	$T_C = 80^\circ\text{C}$	180	A
$I_{CM}$	$T_C = 80^\circ\text{C}, t_p = 1 \text{ ms}$	360	A
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = \pm 15 \text{ V}, V_{CE} = V_{CES}, T_J = 125^\circ\text{C}$ $R_G = 6.8 \Omega, \text{ non repetitive}$	10	$\mu\text{s}$
<b>RBSOA</b>	$V_{GE} = \pm 15 \text{ V}, T_J = 125^\circ\text{C}, R_G = 6.8 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 360$ $V_{CEK} \leq V_{CES}$	A
$P_{tot}$	$T_C = 25^\circ\text{C}$	1130	W
$T_J$		150	$^\circ\text{C}$
$T_{stg}$		-40 ... +150	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$ Insulating material: $\text{Al}_2\text{O}_3$	4000 4800	V~ V~
$M_d$	Mounting torque (module)  (terminals)	2.25-2.75 20-25 2.5-3.7 22-33	Nm lb.in. Nm lb.in.
$d_s$	Creepage distance on surface	10	mm
$d_A$	Strike distance through air	9.6	mm
$a$	Max. allowable acceleration	50	$\text{m/s}^2$
<b>Weight</b>	Typical	250 8.8	g oz.

### Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy parallelling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- package with DCB ceramic base plate
- isolation voltage 4800 V
- UL registered E72873

### Advantages

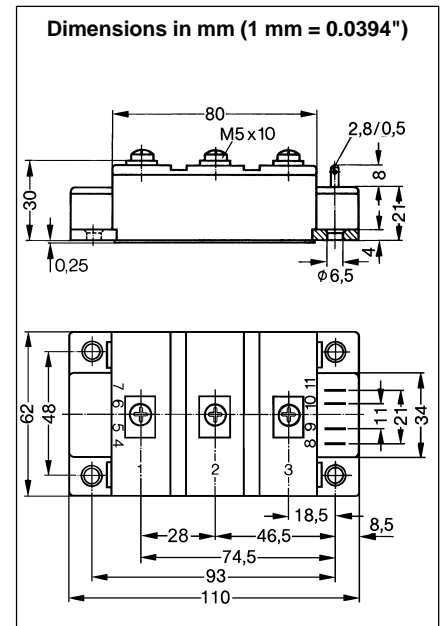
- space and weight savings
- reduced protection circuits

### Typical Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

Data according to a single IGBT/FRED unless otherwise stated.

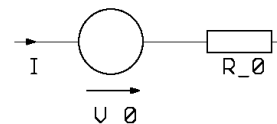
Symbol	Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 6\text{ mA}, V_{CE} = V_{GE}$	4.5		6.5 V
$I_{CES}$	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		15	10 mA mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 700\text{ nA}$
$V_{CE(sat)}$	$I_C = 150\text{ A}, V_{GE} = 15\text{ V}$		2.2	2.7 V
$C_{ies}$	} $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		11	nF
$C_{oes}$			1.5	nF
$C_{res}$			0.65	nF
$t_{d(on)}$	} <b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 150\text{ A}, V_{GE} = \pm 15\text{ V}$ $V_{CE} = 600\text{ V}, R_G = 6.8\ \Omega$		100	ns
$t_r$			50	ns
$t_{d(off)}$			650	ns
$t_f$			50	ns
$E_{on}$			24.2	mJ
$E_{off}$			21	mJ
$R_{thJC}$				0.11 K/W
$R_{thJS}$	with heatsink compound		0.22	K/W



Reverse Diode (FRED)	Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = 150\text{ A}, V_{GE} = 0\text{ V},$ $I_F = 150\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$		2.2 1.8	2.5 V 1.9 V
$I_F$	$T_C = 25^\circ\text{C}$ $T_C = 80^\circ\text{C}$			300 A 200 A
$I_{RM}$	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}, -di_F/dt = 1200\text{ A}/\mu\text{s}$		125	A
$t_{rr}$	$T_J = 125^\circ\text{C}, V_R = 600\text{ V}$		200	ns
$R_{thJC}$				0.23 K/W
$R_{thJS}$	with heatsink compound		0.45	K/W

### Equivalent Circuits for Simulation

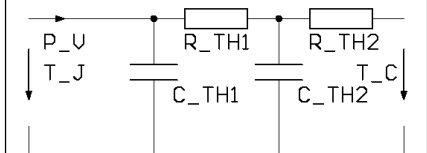
#### Conduction



IGBT (typ. at  $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$ )  
 $V_o = 1.5\text{ V}; R_o = 7.0\text{ m}\Omega$

Free Wheeling Diode (typ. at  $T_J = 125^\circ\text{C}$ )  
 $V_o = 1.3\text{ V}; R_o = 3.4\text{ m}\Omega$

#### Thermal Response



IGBT (typ.)

$C_{th1} = 0.40\text{ J/K}; R_{th1} = 0.110\text{ K/W}$   
 $C_{th2} = 0.93\text{ J/K}; R_{th2} = 0.003\text{ K/W}$

Free Wheeling Diode (typ.)

$C_{th1} = 0.28\text{ J/K}; R_{th1} = 0.226\text{ K/W}$   
 $C_{th2} = 0.51\text{ J/K}; R_{th2} = 0.005\text{ K/W}$

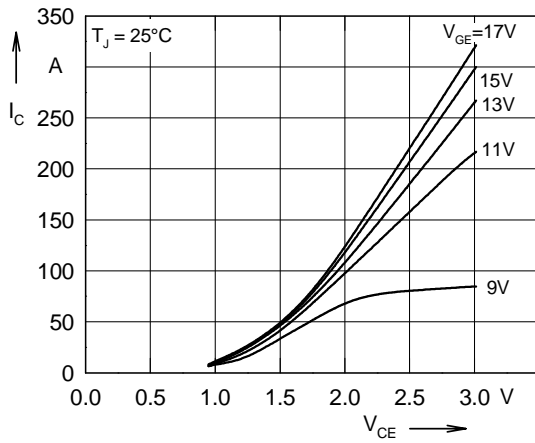


Fig. 1 Typ. output characteristics

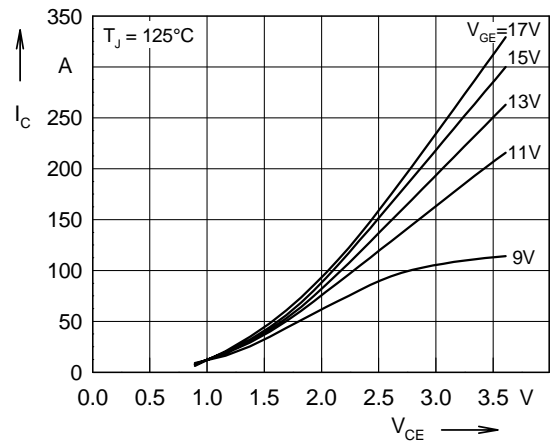


Fig. 2 Typ. output characteristics

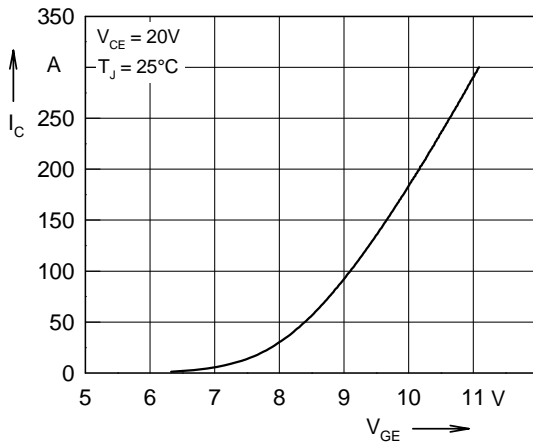


Fig. 3 Typ. transfer characteristics

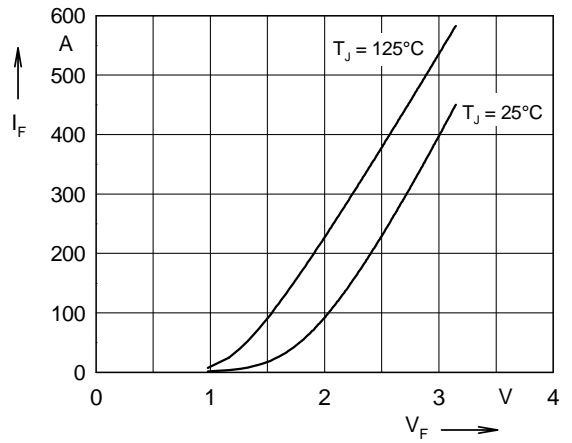


Fig. 4 Typ. forward characteristics of free wheeling diode

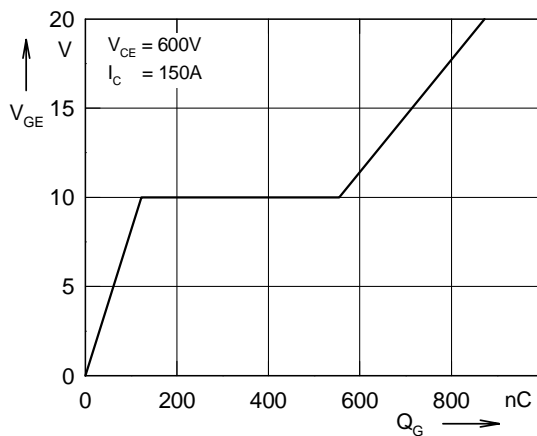


Fig. 5 Typ. turn on gate charge

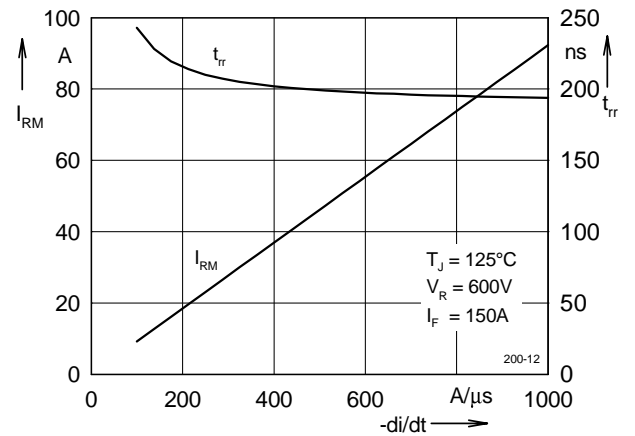


Fig. 6 Typ. turn off characteristics of free wheeling diode

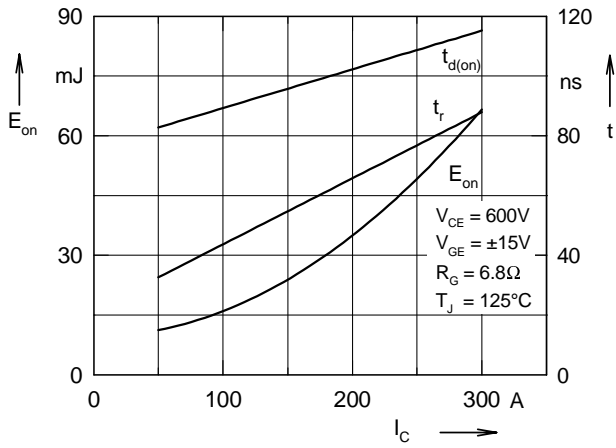


Fig. 7 Typ. turn on energy and switching times versus collector current

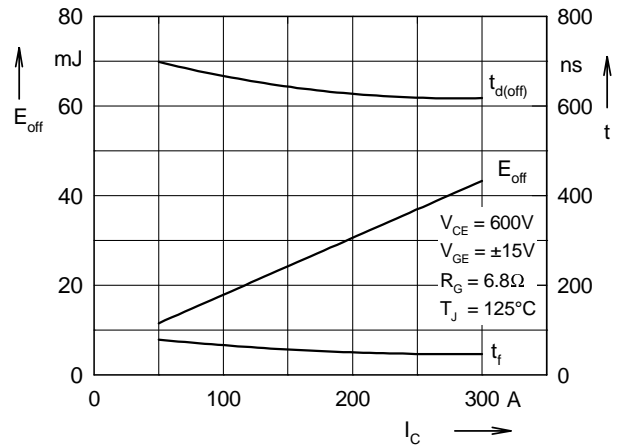


Fig. 8 Typ. turn off energy and switching times versus collector current

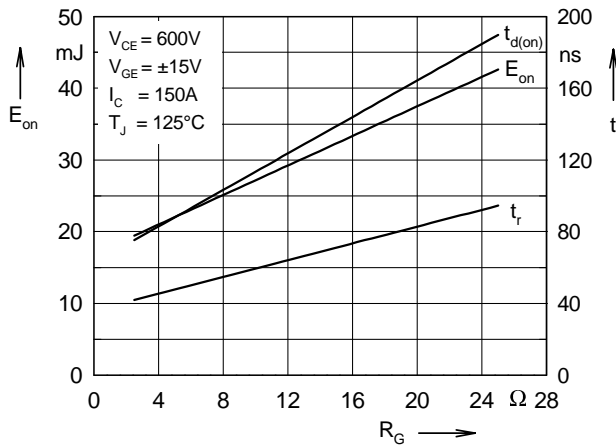


Fig. 9 Typ. turn on energy and switching times versus gate resistor

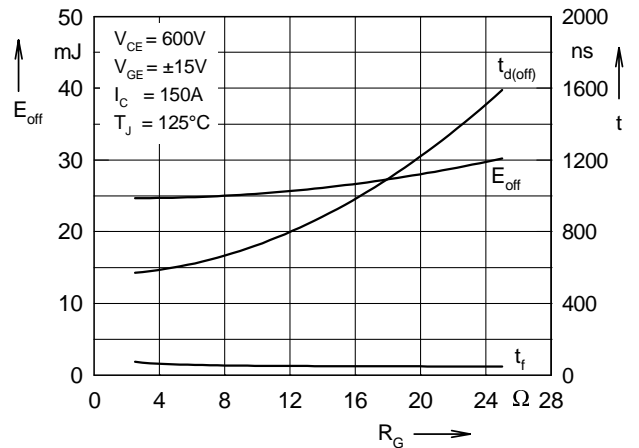


Fig.10 Typ. turn off energy and switching times versus gate resistor

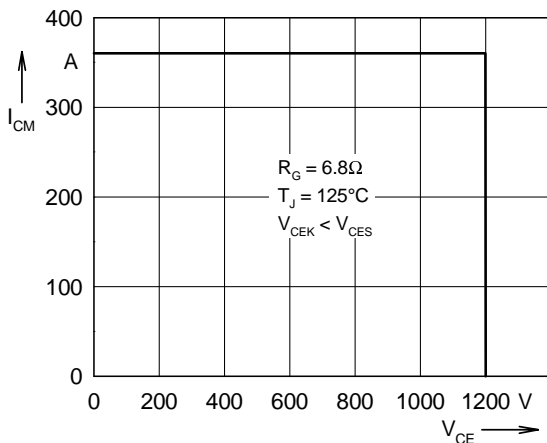


Fig. 11 Reverse biased safe operating area RBSOA

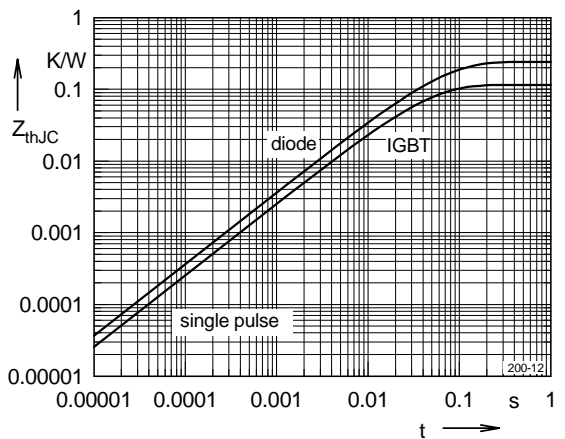


Fig. 12 Typ. transient thermal impedance